

NCEP85T25T

NCE N-Channel Super Trench Power MOSFET

Description

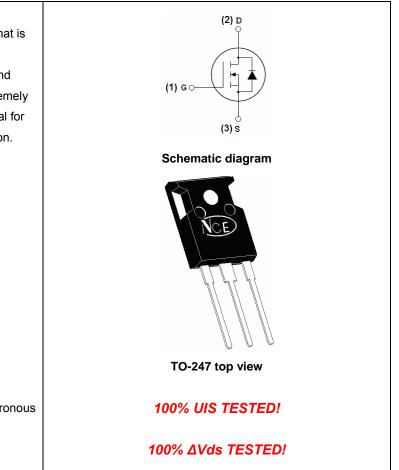
The NCEP85T25T uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =85V,I_D =250A
 R_{DS(ON)} <2.8mΩ @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Package Marking and Ordering Information

	<u> </u>				
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T25T	NCEP85T25T	TO-247	-	-	-

Absolute Maximum Ratings (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	85	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι _D	250	A	
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	180	A	
Pulsed Drain Current	I _{DM}	1000	A	
Maximum Power Dissipation	PD	360	W	
Derating factor		2.4	W/°C	
Single pulse avalanche energy (Note 5)	E _{AS}	2000	mJ	
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C	

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	0.42	°C/W





Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·		•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I _D =100A	-	2.1	2.8	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =100A	-	90	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C _{lss}	N 40) () () (-	10700	-	PF
Output Capacitance	C _{oss}	V _{DS} =40V,V _{GS} =0V,	-	1700	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	76	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	28	-	nS
Turn-on Rise Time	tr	V _{DD} =40V,I _D =100A	-	73	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.6 Ω	-	86	-	nS
Turn-Off Fall Time	t _f		-	33	-	nS
Total Gate Charge	Qg	V 40V/1 400A	-	142		nC
Gate-Source Charge	Q _{gs}	V _{DS} =40V,I _D =100A, V _{GS} =10V	-	56		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	24		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _F = I _S	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	250	А
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-	115		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	320		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ C$,V_DD=42.5V,V_G=10V,L=0.5mH,Rg=25\Omega

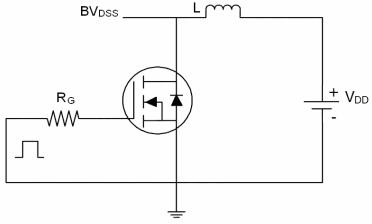


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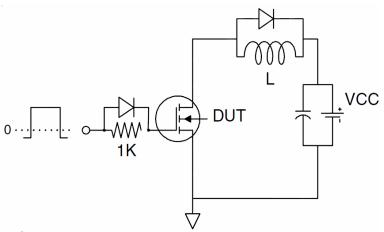




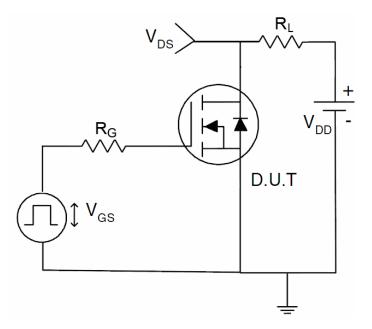
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



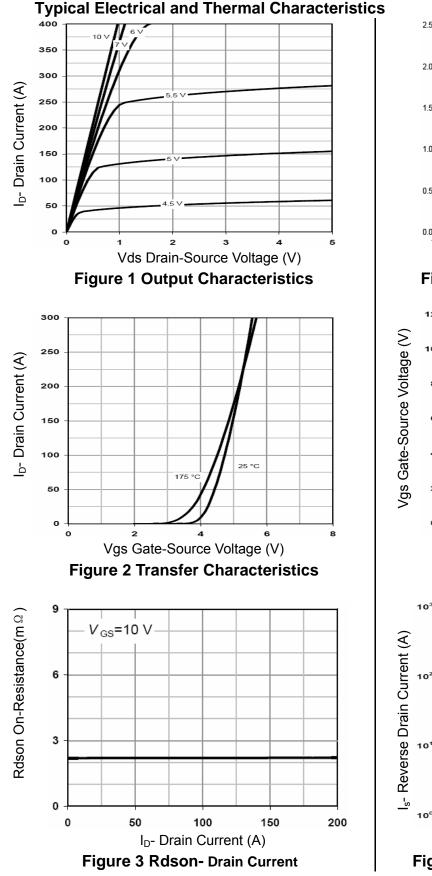
3) Switch Time Test Circuit





NCEP85T25T





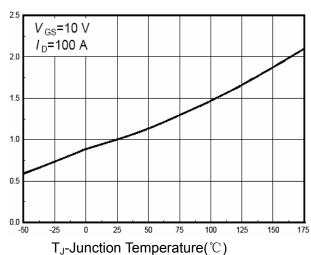
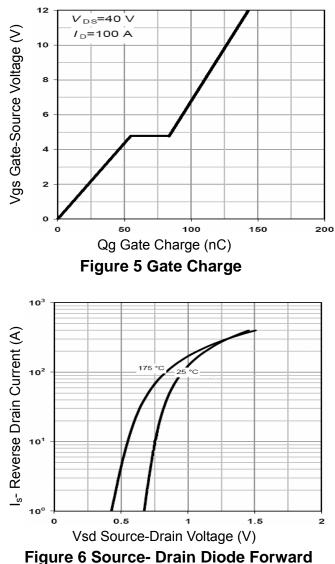


Figure 4 Rdson-JunctionTemperature

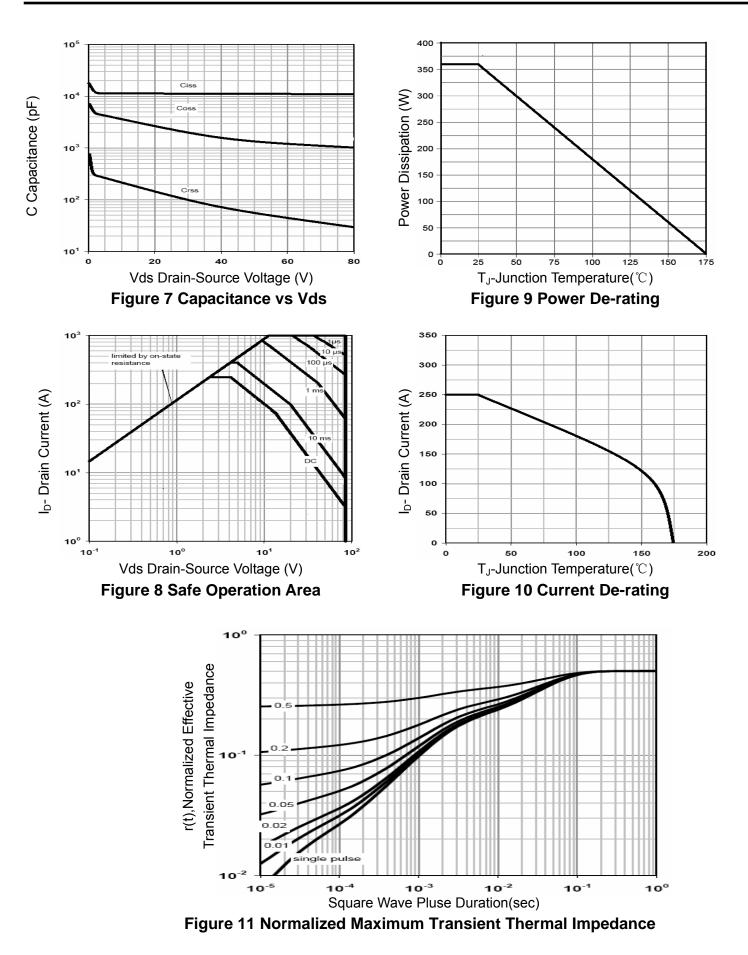




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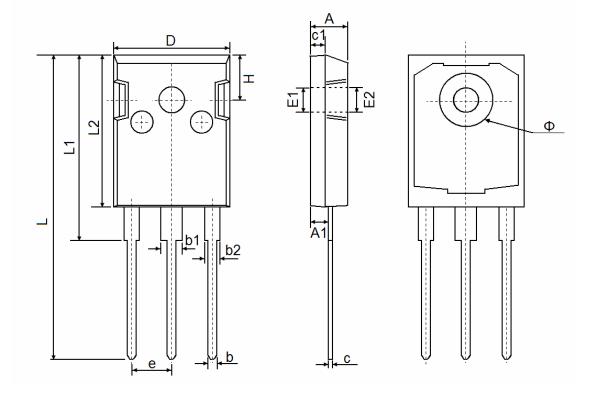


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TO-247 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.850	5.150	0.191	0.200	
A1	2.200	2.600	0.087	0.102	
b	1.000	1.400	0.039	0.055	
b1	2.800	3.200	0.110	0.126	
b2	1.800	2.200	0.071	0.087	
С	0.500	0.700	0.020	0.028	
c1	1.900	2.100	0.075	0.083	
D	15.450	15.750	0.608	0.620	
E1	3.500) REF	0.138 REF		
E2	3.600) REF	0.142 REF		
L	40.900	41.300	1.610	1.626	
L1	24.800	25.100	0.976	0.988	
L2	20.300	20.600	0.799	0.811	
Ф	7.100	7.300	0.280	0.287	
е	5.450 TYP		0.215 TYP		
Н	5.980 REF		0.235	0.235 REF	







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